

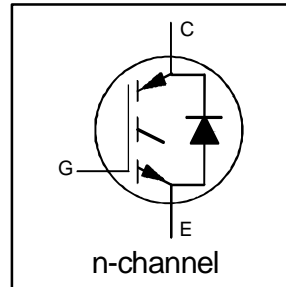
# IRGBC20KD2

INSULATED GATE BIPOLAR TRANSISTOR  
WITH ULTRAFAST SOFT RECOVERY DIODE

Short Circuit Rated  
UltraFast CoPack IGBT

## Features

- Short circuit rated -10 $\mu$ s @125°C,  $V_{GE} = 15V$
  - Switching-loss rating includes all "tail" losses
  - HEXFRED™ soft ultrafast diodes
  - Optimized for high operating frequency (over 5kHz)
- See Fig. 1 for Current vs. Frequency curve

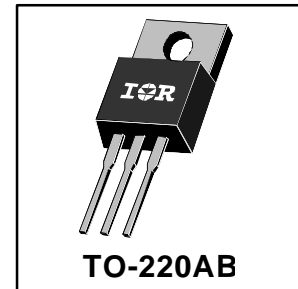


$V_{CES} = 600V$
$V_{CE(sat)} \leq 3.5V$
@ $V_{GE} = 15V, I_C = 6.0A$

## Description

Co-packaged IGBTs are a natural extension of International Rectifier's well known IGBT line. They provide the convenience of an IGBT and an ultrafast recovery diode in one package, resulting in substantial benefits to a host of high-voltage, high-current, applications.

These new short circuit rated devices are especially suited for motor control and other applications requiring short circuit withstand capability.



## Absolute Maximum Ratings

	Parameter	Max.	Units
$V_{CES}$	Collector-to-Emitter Voltage	600	V
$I_C @ T_C = 25^\circ C$	Continuous Collector Current	10	A
$I_C @ T_C = 100^\circ C$	Continuous Collector Current	6.0	
$I_{CM}$	Pulsed Collector Current ①	20	
$I_{LM}$	Clamped Inductive Load Current ②	20	
$I_F @ T_C = 100^\circ C$	Diode Continuous Forward Current	7.0	
$I_{FM}$	Diode Maximum Forward Current	20	
$t_{sc}$	Short Circuit Withstand Time	10	$\mu$ s
$V_{GE}$	Gate-to-Emitter Voltage	$\pm 20$	V
$P_D @ T_C = 25^\circ C$	Maximum Power Dissipation	60	W
$P_D @ T_C = 100^\circ C$	Maximum Power Dissipation	24	
$T_J$	Operating Junction and	-55 to +150	$^\circ$ C
$T_{STG}$	Storage Temperature Range		
	Soldering Temperature, for 10 sec.		
	Mounting Torque, 6-32 or M3 Screw.	10 lbf•in (1.1 N•m)	

## Thermal Resistance

	Parameter	Min.	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case - IGBT	—	—	2.1	$^\circ$ C/W
$R_{\theta JC}$	Junction-to-Case - Diode	—	—	3.5	
$R_{\theta CS}$	Case-to-Sink, flat, greased surface	—	0.50	—	
$R_{\theta JA}$	Junction-to-Ambient, typical socket mount	—	—	80	
Wt	Weight	—	2 (0.07)	—	g (oz)

**Electrical Characteristics @  $T_J = 25^\circ\text{C}$  (unless otherwise specified)**

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)CES}$	Collector-to-Emitter Breakdown Voltage ③	600	—	—	V	$V_{GE} = 0V, I_C = 250\mu\text{A}$
$\Delta V_{(BR)CES}/\Delta T_J$	Temp. Coeff. of Breakdown Voltage	—	0.37	—	V/°C	$V_{GE} = 0V, I_C = 1.0\text{mA}$
$V_{CE(on)}$	Collector-to-Emitter Saturation Voltage	—	2.4	3.5	V	$I_C = 6.0\text{A}$ $I_C = 10\text{A}$ $I_C = 6.0\text{A}, T_J = 150^\circ\text{C}$ See Fig. 2, 5
		—	3.6	—		
		—	2.8	—		
$V_{GE(th)}$	Gate Threshold Voltage	3.0	—	5.5		$V_{CE} = V_{GE}, I_C = 250\mu\text{A}$
$\Delta V_{GE(th)}/\Delta T_J$	Temperature Coeff. of Threshold Voltage	—	-11	—	mV/°C	$V_{CE} = V_{GE}, I_C = 250\mu\text{A}$
$g_{fe}$	Forward Transconductance ④	1.9	3.3	—	S	$V_{CE} = 100V, I_C = 6.0\text{A}$
$I_{CES}$	Zero Gate Voltage Collector Current	—	—	250	$\mu\text{A}$	$V_{GE} = 0V, V_{CE} = 600V$
		—	—	1700		$V_{GE} = 0V, V_{CE} = 600V, T_J = 150^\circ\text{C}$
$V_{FM}$	Diode Forward Voltage Drop	—	1.4	1.7	V	$I_C = 8.0\text{A}$ See Fig. 13
		—	1.4	1.7		$I_C = 8.0\text{A}, T_J = 150^\circ\text{C}$
$I_{GES}$	Gate-to-Emitter Leakage Current	—	—	$\pm 100$	nA	$V_{GE} = \pm 20V$

**Switching Characteristics @  $T_J = 25^\circ\text{C}$  (unless otherwise specified)**

	Parameter	Min.	Typ.	Max.	Units	Conditions
$Q_g$	Total Gate Charge (turn-on)	—	17	26	nC	$I_C = 6.0\text{A}$ $V_{CC} = 480V$ See Fig. 8
$Q_{ge}$	Gate - Emitter Charge (turn-on)	—	4.3	6.8		
$Q_{gc}$	Gate - Collector Charge (turn-on)	—	6.4	11		
$t_{d(on)}$	Turn-On Delay Time	—	59	—	ns	$T_J = 25^\circ\text{C}$ $I_C = 6.0\text{A}, V_{CC} = 480V$ $V_{GE} = 15V, R_G = 50\Omega$ Energy losses include "tail" and diode reverse recovery. See Fig. 9, 10, 11, 18
$t_r$	Rise Time	—	38	—		
$t_{d(off)}$	Turn-Off Delay Time	—	110	210		
$t_f$	Fall Time	—	80	120		
$E_{on}$	Turn-On Switching Loss	—	0.28	—	mJ	
$E_{off}$	Turn-Off Switching Loss	—	0.15	—		
$E_{ts}$	Total Switching Loss	—	0.43	0.90		
$t_{sc}$	Short Circuit Withstand Time	10	—	—	$\mu\text{s}$	$V_{CC} = 360V, T_J = 125^\circ\text{C}$ $V_{GE} = 15V, R_G = 50\Omega, V_{CPK} < 500V$
$t_{d(on)}$	Turn-On Delay Time	—	52	—	ns	$T_J = 150^\circ\text{C}$ , See Fig. 9, 10, 11, 18 $I_C = 6.0\text{A}, V_{CC} = 480V$ $V_{GE} = 15V, R_G = 50\Omega$ Energy losses include "tail" and diode reverse recovery.
$t_r$	Rise Time	—	35	—		
$t_{d(off)}$	Turn-Off Delay Time	—	170	—		
$t_f$	Fall Time	—	170	—		
$E_{ts}$	Total Switching Loss	—	0.7	—	mJ	
$L_E$	Internal Emitter Inductance	—	7.5	—	nH	Measured 5mm from package
$C_{ies}$	Input Capacitance	—	350	—	pF	$V_{GE} = 0V$ $V_{CC} = 30V$ See Fig. 7 $f = 1.0\text{MHz}$
$C_{oes}$	Output Capacitance	—	50	—		
$C_{res}$	Reverse Transfer Capacitance	—	4.7	—		
$t_{rr}$	Diode Reverse Recovery Time	—	37	55	ns	$T_J = 25^\circ\text{C}$ See Fig. 14 $T_J = 125^\circ\text{C}$
		—	55	90		
$I_{rr}$	Diode Peak Reverse Recovery Current	—	3.5	5.0	A	$T_J = 25^\circ\text{C}$ See Fig. 15 $T_J = 125^\circ\text{C}$
		—	4.5	8.0		
$Q_{rr}$	Diode Reverse Recovery Charge	—	65	138	nC	$T_J = 25^\circ\text{C}$ See Fig. 16 $T_J = 125^\circ\text{C}$
		—	124	360		
$di_{(rec)M}/dt$	Diode Peak Rate of Fall of Recovery During $t_b$	—	240	—	A/ $\mu\text{s}$	$T_J = 25^\circ\text{C}$ See Fig. 17 $T_J = 125^\circ\text{C}$
		—	210	—		

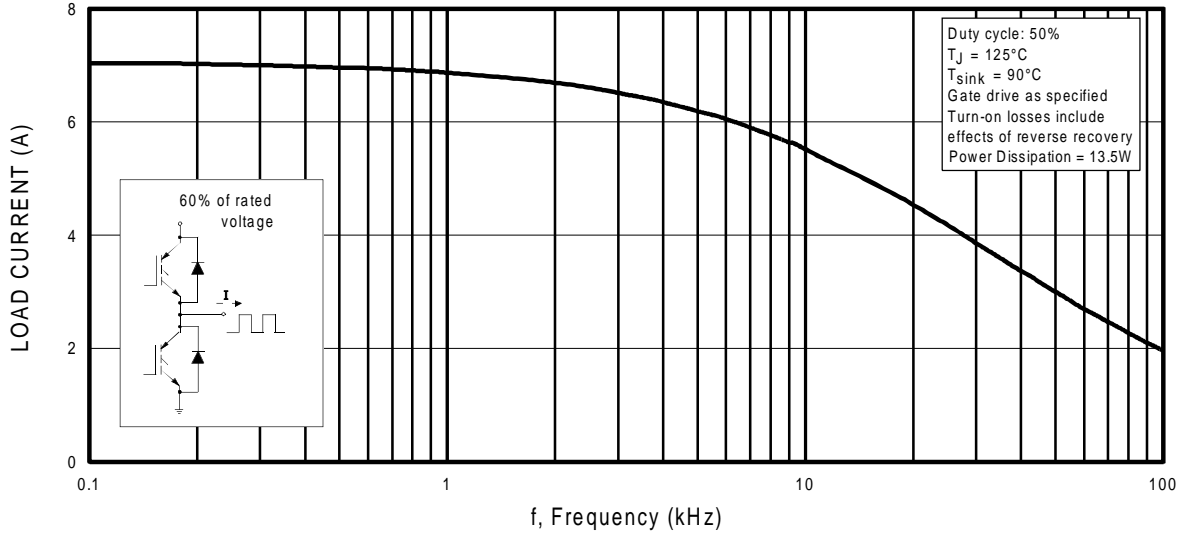
**Notes:**

① Repetitive rating;  $V_{GE}=20V$ , pulse width limited by max. junction temperature. ( See fig. 20 )

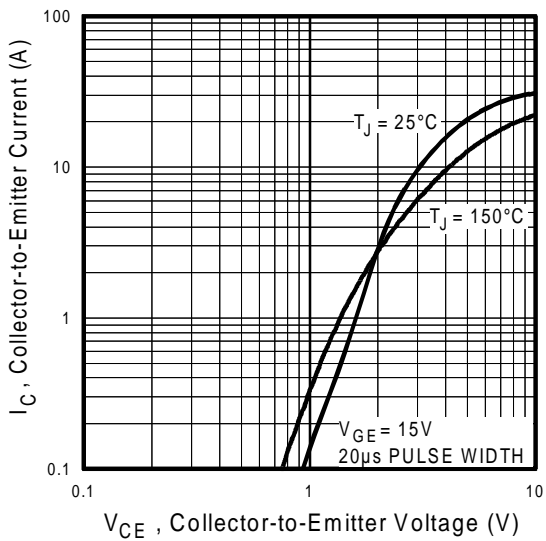
②  $V_{CC}=80\%(V_{CES}), V_{GE}=20V, L=10\mu\text{H}, R_G=50\Omega$ , ( See fig. 19 )

③ Pulse width  $\leq 80\mu\text{s}$ ; duty factor  $\leq 0.1\%$ .

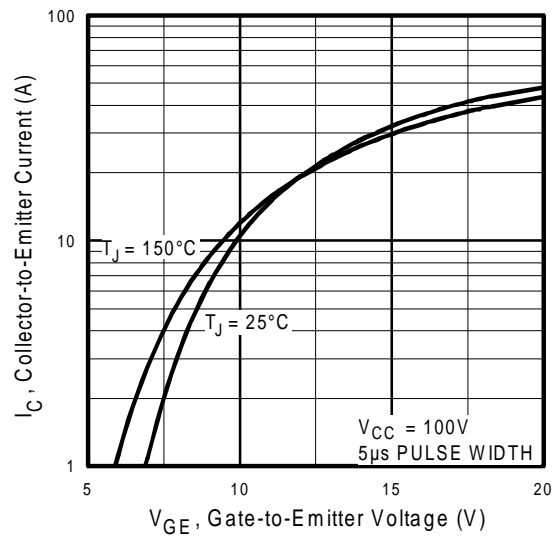
④ Pulse width 5.0 $\mu\text{s}$ , single shot.



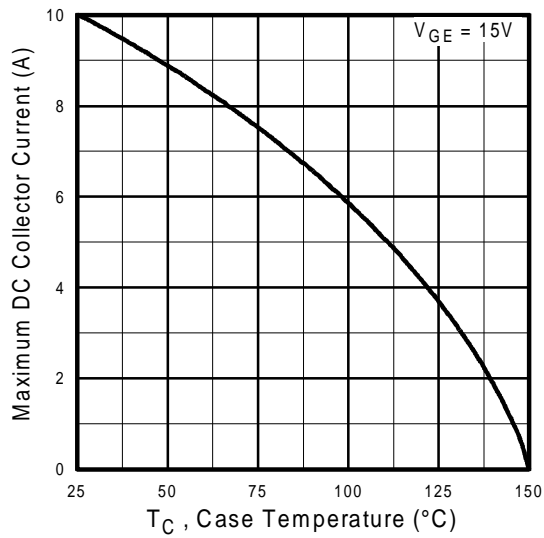
**Fig. 1 - Typical Load Current vs. Frequency**  
(Load Current =  $I_{RMS}$  of fundamental)



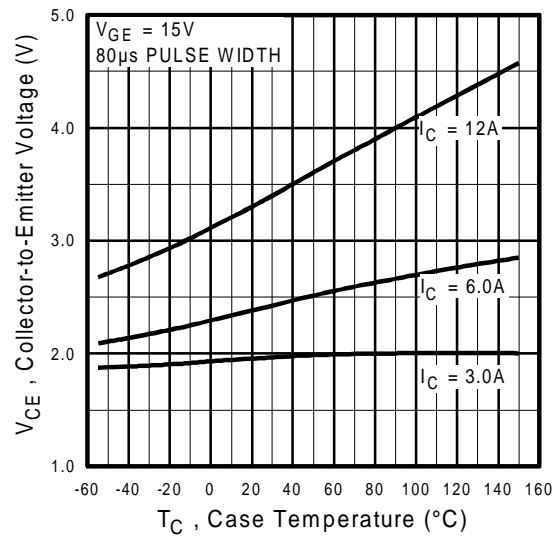
**Fig. 2 - Typical Output Characteristics**



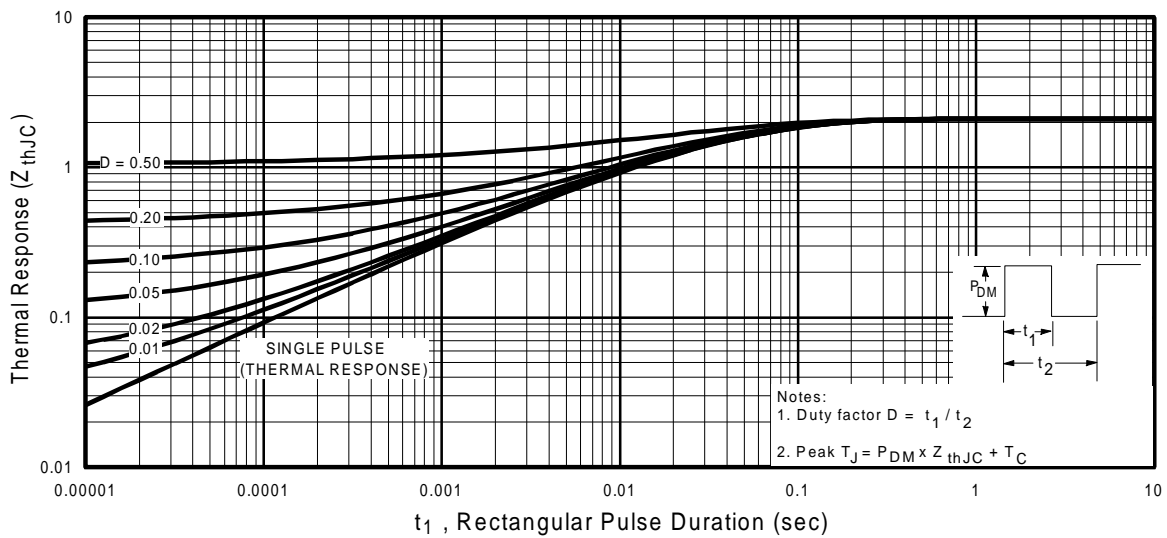
**Fig. 3 - Typical Transfer Characteristics**



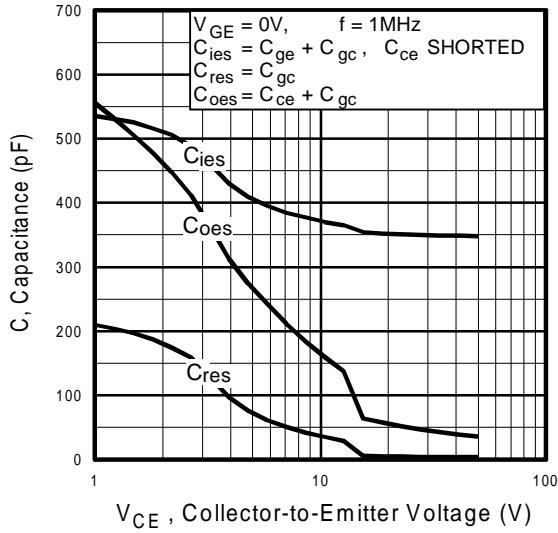
**Fig. 4 - Maximum Collector Current vs. Case Temperature**



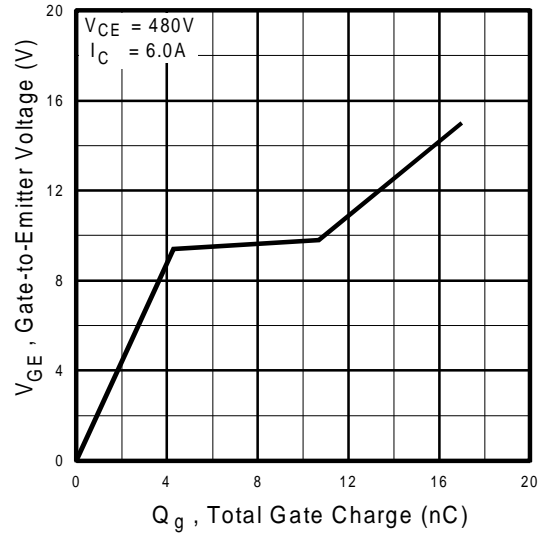
**Fig. 5 - Collector-to-Emitter Voltage vs. Case Temperature**



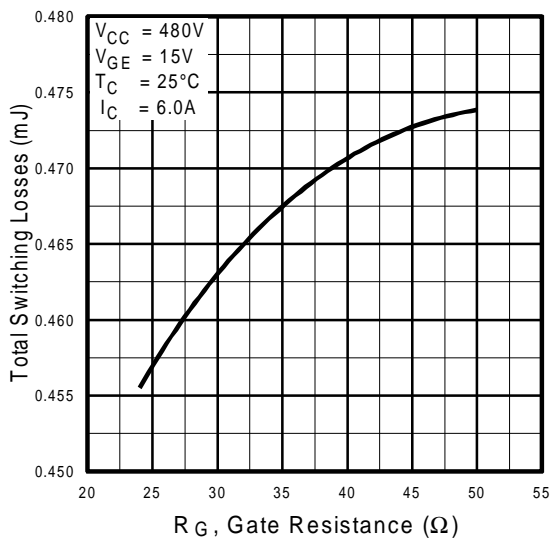
**Fig. 6 - Maximum IGBT Effective Transient Thermal Impedance, Junction-to-Case**



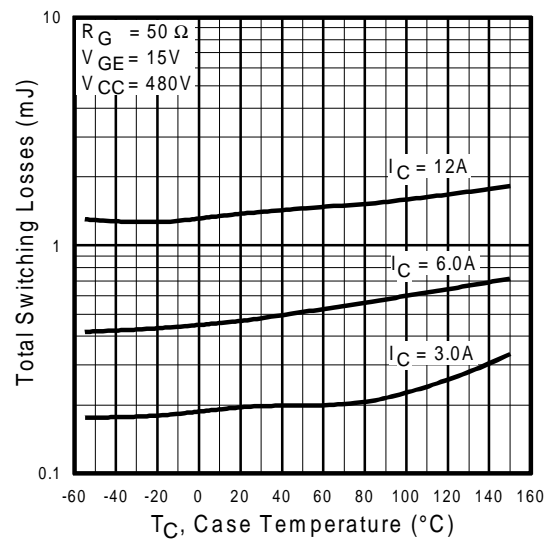
**Fig. 7** - Typical Capacitance vs. Collector-to-Emitter Voltage



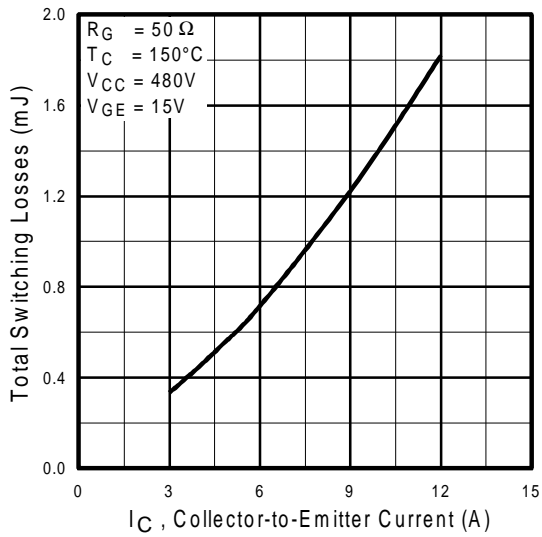
**Fig. 8** - Typical Gate Charge vs. Gate-to-Emitter Voltage



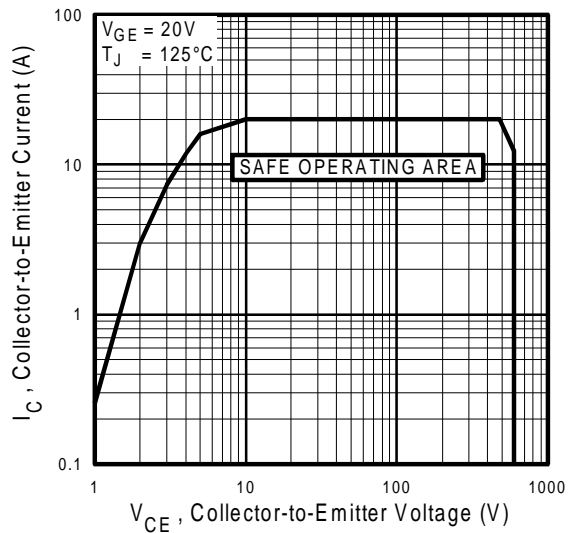
**Fig. 9** - Typical Switching Losses vs. Gate Resistance



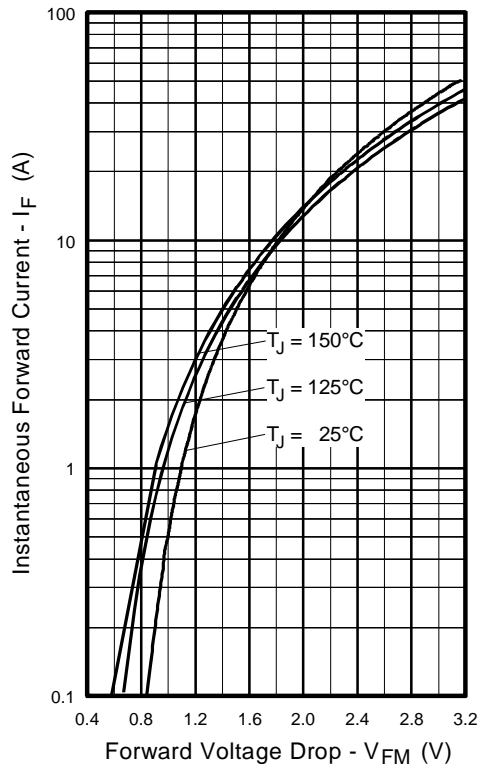
**Fig. 10** - Typical Switching Losses vs. Case Temperature



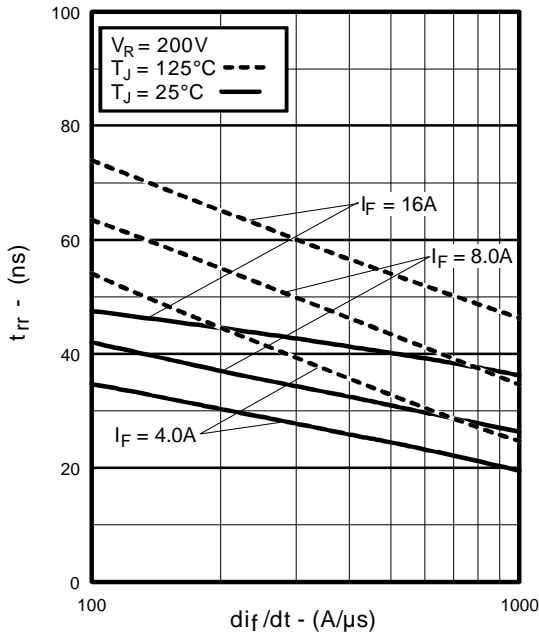
**Fig. 11** - Typical Switching Losses vs. Collector-to-Emitter Current



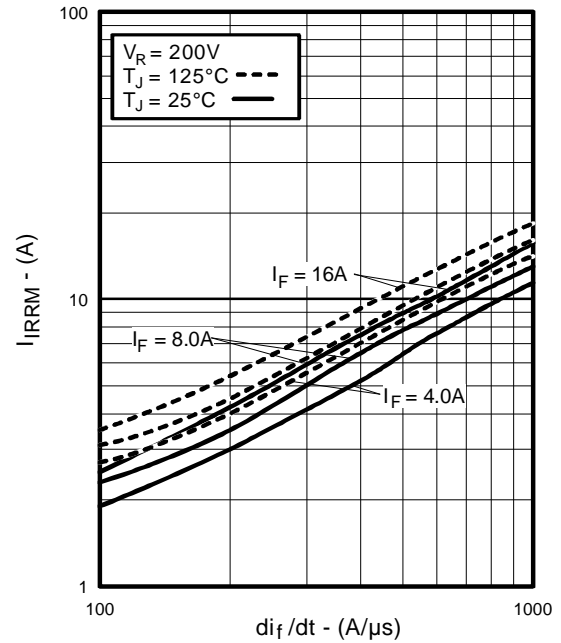
**Fig. 12** - Turn-Off SOA



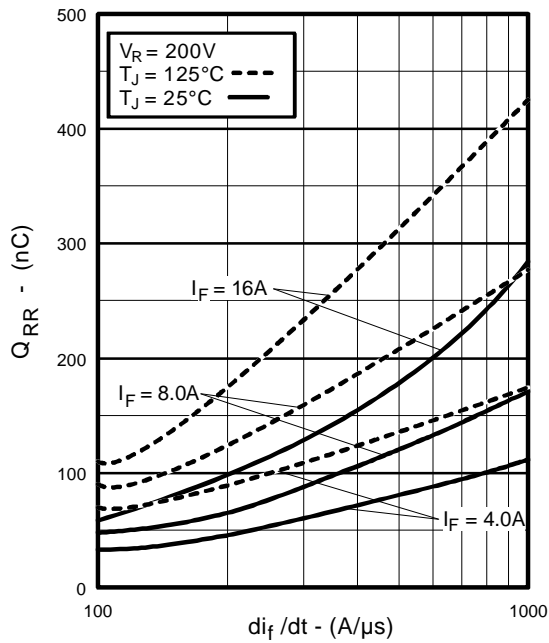
**Fig. 13** - Maximum Forward Voltage Drop vs. Instantaneous Forward Current



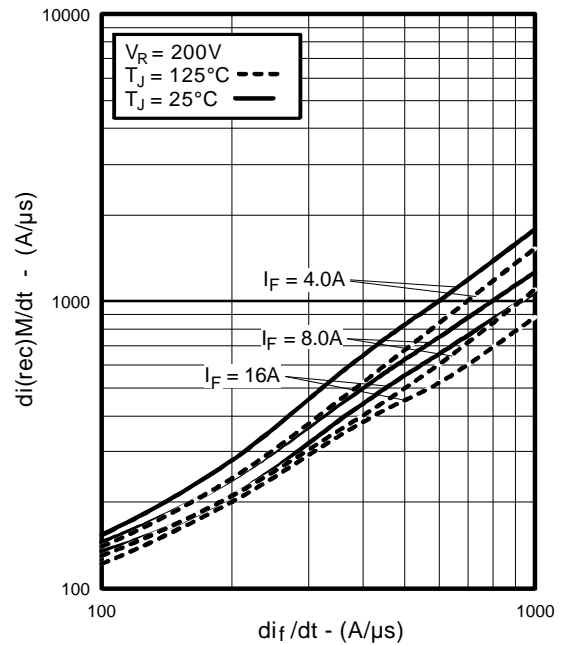
**Fig. 14** - Typical Reverse Recovery vs.  $di_f/dt$



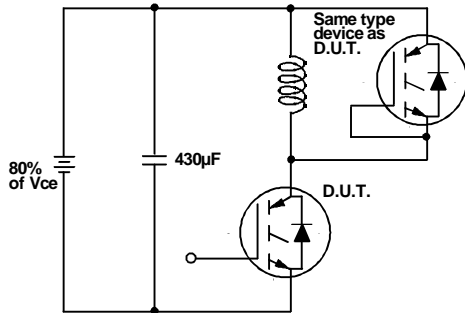
**Fig. 15** - Typical Recovery Current vs.  $di_f/dt$



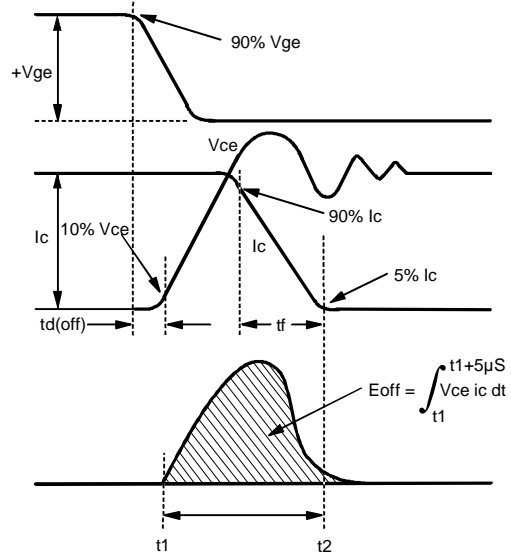
**Fig. 16** - Typical Stored Charge vs.  $di_f/dt$



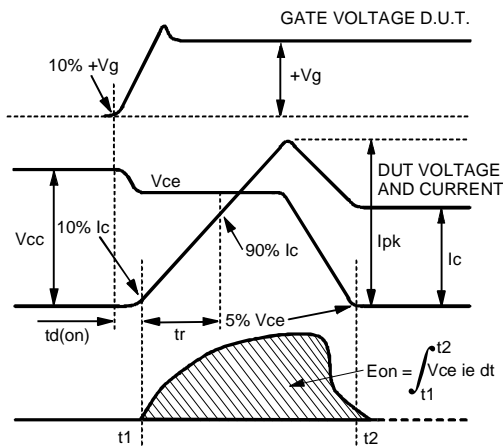
**Fig. 17** - Typical  $di_{(rec)M}/dt$  vs.  $di_f/dt$



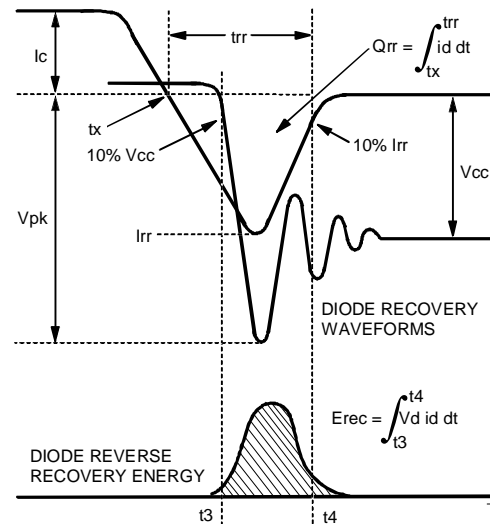
**Fig. 18a** - Test Circuit for Measurement of  $I_{LM}$ ,  $E_{on}$ ,  $E_{off}(\text{diode})$ ,  $t_{rr}$ ,  $Q_{rr}$ ,  $I_{rr}$ ,  $t_{d(on)}$ ,  $t_r$ ,  $t_{d(off)}$ ,  $t_f$



**Fig. 18b** - Test Waveforms for Circuit of Fig. 18a, Defining  $E_{off}$ ,  $t_{d(off)}$ ,  $t_f$



**Fig. 18c** - Test Waveforms for Circuit of Fig. 18a, Defining  $E_{on}$ ,  $t_{d(on)}$ ,  $t_r$



**Fig. 18d** - Test Waveforms for Circuit of Fig. 18a, Defining  $E_{rec}$ ,  $t_{rr}$ ,  $Q_{rr}$ ,  $I_{rr}$

**Refer to Section D for the following:  
Appendix D: Section D - page D-6**

- Fig. 18e - Macro Waveforms for Test Circuit of Fig. 18a
- Fig. 19 - Clamped Inductive Load Test Circuit
- Fig. 20 - Pulsed Collector Current Test Circuit